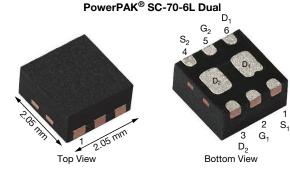
RoHS

COMPLIANT

HALOGEN FREE

# **Dual N-Channel 30 V (D-S) MOSFET**

PRODUCT SUMMARY									
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω) MAX.	I <sub>D</sub> (A)	Q <sub>g</sub> (TYP.)						
30	0.058 at V <sub>GS</sub> = 4.5 V	4.5 <sup>a</sup>							
	0.065 at V <sub>GS</sub> = 2.5 V	4.5 <sup>a</sup>	3.6 nC						
	0.077 at V <sub>GS</sub> = 1.8 V	4.5 <sup>a</sup>							



Marking Code: CL **Ordering Information:** 

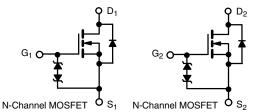
SiA918EDJ-T1-GE3 (lead (Pb)-free and halogen free)

#### **FEATURES**

- TrenchFET® power MOSFET
- Thermally enhanced PowerPAK® SC-70 package
  - Small footprint area
  - Low on-resistance
- Typical ESD protection: 1000 V (HBM)
- 100 % R<sub>a</sub> tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

## **APPLICATIONS**

- Portable devices such as smart phones, tablet PCs and mobile computing
  - Load switch
  - DC/DC converter
  - Power management



PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-Source Voltage	V <sub>DS</sub>	30	V		
Gate-Source Voltage	$V_{GS}$	V <sub>GS</sub> ± 8			
	T <sub>C</sub> = 25 °C		4.5 <sup>a</sup>		
Continuous Dusin Comment (T. 150 °C)	T <sub>C</sub> = 70 °C		4.5 <sup>a</sup>		
Continuous Drain Current (T <sub>J</sub> = 150 °C)	T <sub>A</sub> = 25 °C	I <sub>D</sub>	4.4 b, c		
	T <sub>A</sub> = 70 °C		3.5 <sup>b, c</sup>	Α	
Pulsed Drain Current (t = 100 μs)	I <sub>DM</sub>	15			
Osadis as a Osama Basis Bisala Osamal	T <sub>C</sub> = 25 °C		4.5 <sup>a</sup>		
Continuous Source-Drain Diode Current	T <sub>A</sub> = 25 °C	ls	1.6 <sup>b, c</sup>		
	T <sub>C</sub> = 25 °C		7.8		
Manian on Danian Disabation	T <sub>C</sub> = 70 °C	_	5	14/	
Maximum Power Dissipation	T <sub>A</sub> = 25 °C	P <sub>D</sub>	1.9 <sup>b, c</sup>	W	
	T <sub>A</sub> = 70 °C		1.2 <sup>b, c</sup>		
Operating Junction and Storage Temperatur	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	00		
Soldering Recommendations (Peak Tempera		260	°C		

THERMAL RESISTANCE RATINGS									
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT				
Maximum Junction-to-Ambient b, f	p-Ambient $b, f$ $t \le 5$ s $R_{thJA}$ 52 65		65	°C/W					
Maximum Junction-to-Case (Drain)	Steady State	R <sub>thJC</sub>	12.5	16	- C/W				

#### **Notes**

- a. Package limited.
- b. Surface mounted on 1" x 1" FR4 board.
- See solder profile (www.vishav.com/doc?73257). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
- f. Maximum under steady state condition is 110 °C/W.

# Vishay Siliconix

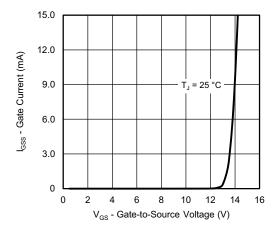
	nless otherw	,	MAINI	TVD	MAN	TIMIT	
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static			1	T	I	.,	
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$	30	-	-	V	
V <sub>DS</sub> Temperature Coefficient	$\Delta V_{DS}/T_{J}$	I <sub>D</sub> = 250 μA	-	28	-	mV/°C	
V <sub>GS(th)</sub> Temperature Coefficient	$\Delta V_{GS(th)}/T_J$		-	-2.4	-		
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \mu A$	0.4	-	0.9	V	
Gate-Source Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 4.5 \text{ V}$	-	-	± 0.5	μΑ	
	1655	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$	-	-	± 5		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	1	μ, ,	
Zoro dato voltago Brain Garront	יטא	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 55 ^{\circ}\text{C}$	-	-	10		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	10	-	-	Α	
		$V_{GS} = 4.5 \text{ V}, I_D = 3 \text{ A}$	-	0.046	0.058		
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	$V_{GS} = 2.5 \text{ V}, I_D = 3 \text{ A}$	-	0.050	0.065	Ω	
		V <sub>GS</sub> = 1.8 V, I <sub>D</sub> = 1 A	-	0.055	0.077		
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 3 A	-	14	-	S	
Dynamic <sup>b</sup>							
T		$V_{DS} = 15 \text{ V}, V_{GS} = 8 \text{ V}, I_D = 10 \text{ A}$	-	6.2	9.5	nC	
Total Gate Charge	$Q_g$	V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 10 A	-	3.6	5.5		
Gate-Source Charge	Q <sub>gs</sub>		-	0.45	-		
Gate-Drain Charge	Q <sub>gd</sub>		-	0.53	-		
Gate Resistance	R <sub>g</sub>	f = 1 MHz	0.9	4.3	8.6	Ω	
Turn-On Delay Time	t <sub>d(on)</sub>		-	5	10		
Rise Time	t <sub>r</sub>	$V_{DD} = 15 \text{ V}, R_{L} = 5 \Omega$	-	30	60		
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D \cong 3 \text{ A}, V_{GEN} = 4.5 \text{ V}, R_g = 1 \Omega$	-	30	60		
Fall Time	t <sub>f</sub>		-	41	80		
Turn-On Delay Time	t <sub>d(on)</sub>		-	2	5	ns	
Rise Time	t <sub>r</sub>	$V_{DD} = 15 \text{ V}, R_L = 5 \Omega$	-	23	50		
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D\cong 3$ A, $V_{GEN}=8$ V, $R_g=1~\Omega$	-	11	20		
Fall Time	t <sub>f</sub>		-	26	50		
<b>Drain-Source Body Diode Characteristic</b>	s						
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	-	-	4.5	Δ.	
Pulse Diode Forward Current	e Diode Forward Current I <sub>SM</sub>		-	-	15	Α	
Body Diode Voltage	$V_{SD}$	$I_{S} = 3 \text{ A}, V_{GS} = 0 \text{ V}$	-	0.84	1.2	V	
Body Diode Reverse Recovery Time	t <sub>rr</sub>		-	11	20	ns	
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>	$I_F = 3 A$ , $dI/dt = 100 A/\mu s$ ,	-	4.4	10	nC	
Reverse Recovery Fall Time	t <sub>a</sub>	T <sub>J</sub> = 25 °C	-	8	-	ns	
Reverse Recovery Rise Time	t <sub>b</sub>		_	3	-		

### Notes

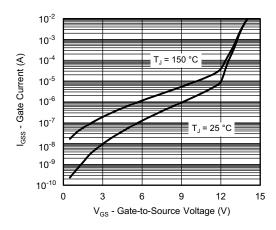
- a. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

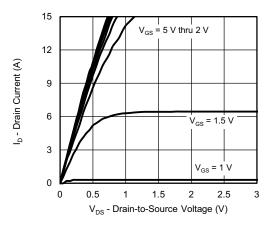




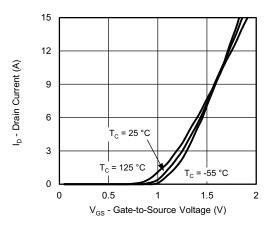
Gate Current vs. Gate-Source Voltage



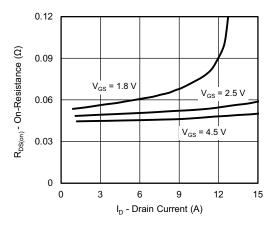
**Gate Current vs. Gate-Source Voltage** 



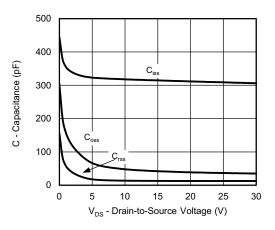
**Output Characteristics** 



**Transfer Characteristics** 

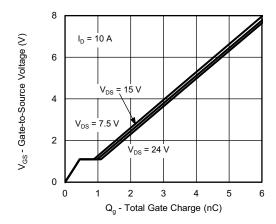


On-Resistance vs. Drain Current and Gate Voltage

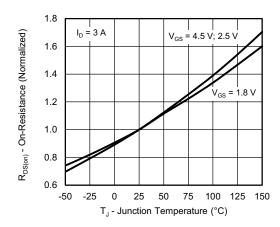


Capacitance

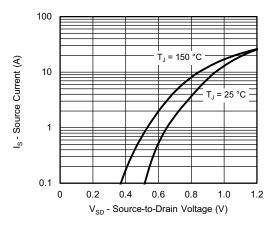




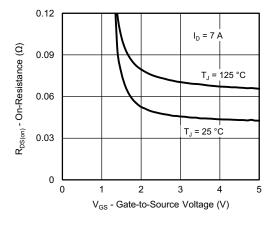
#### **Gate Charge**



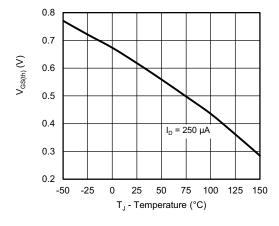
On-Resistance vs. Junction Temperature



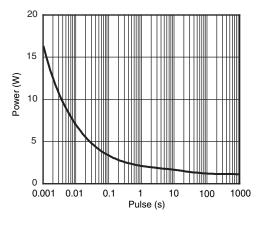
Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage

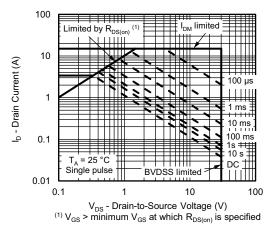


**Threshold Voltage** 

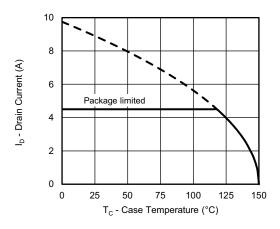


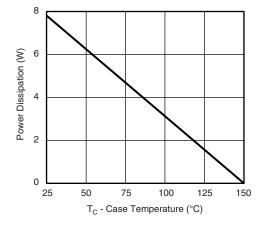
Single Pulse Power (Junction-to-Ambient)





Safe Operating Area, Junction-to-Ambient





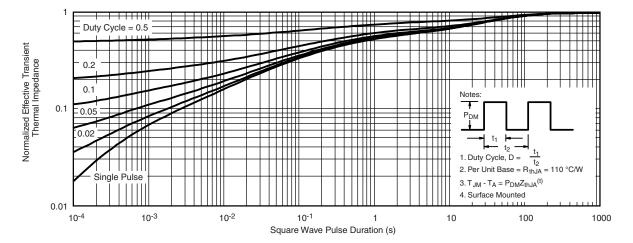
Current Derating a

**Power Derating** 

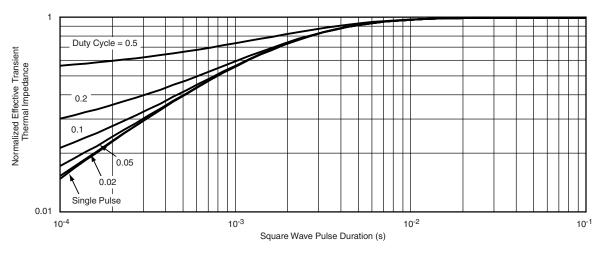
#### Note

a. The power dissipation P<sub>D</sub> is based on T<sub>J</sub> (max.) = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.





#### Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg279034">www.vishay.com/ppg279034</a>.





Vishay Siliconix

# PowerPAK® SC70-6L





BACKSIDE VIEW OF SINGLE

BACKSIDE VIEW OF DUAL



- All dimensions are in millimeters
  Package outline exclusive of mold flash and metal burr
  Package outline inclusive of plating

	SINGLE PAD						DUAL PAD						
DIM	MILLIMETERS			INCHES			MILLIMETERS			INCHES			
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	
Α	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032	
A1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002	
b	0.23	0.30	0.38	0.009	0.012	0.015	0.23	0.30	0.38	0.009	0.012	0.015	
С	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010	
D	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085	
D1	0.85	0.95	1.05	0.033	0.037	0.041	0.513	0.613	0.713	0.020	0.024	0.028	
D2	0.135	0.235	0.335	0.005	0.009	0.013							
Е	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085	
E1	1.40	1.50	1.60	0.055	0.059	0.063	0.85	0.95	1.05	0.033	0.037	0.041	
E2	0.345	0.395	0.445	0.014	0.016	0.018							
E3	0.425	0.475	0.525	0.017	0.019	0.021							
е		0.65 BSC			0.026 BSC	;	0.65 BSC			0.026 BSC			
K		0.275 TYP			0.011 TYP		0.275 TYP		0.011 TYP				
K1		0.400 TYP			0.016 TYP			0.320 TYP			0.013 TYP		
K2		0.240 TYP		0.009 TYP		0.252 TYP		0.010 TYP					
К3		0.225 TYP		0.009 TYP					•	•			
K4		0.355 TYP		0.014 TYP									
L	0.175	0.275	0.375	0.007	0.011	0.015	0.175	0.275	0.375	0.007	0.011	0.015	
T							0.05	0.10	0.15	0.002	0.004	0.006	

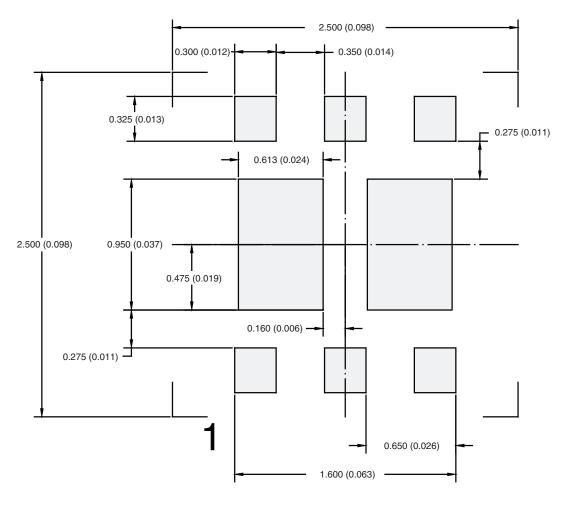
ECN: C-07431 - Rev. C, 06-Aug-07

DWG: 5934

06-Aug-07



# RECOMMENDED PAD LAYOUT FOR PowerPAK® SC70-6L Dual



Dimensions in mm (inches)

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